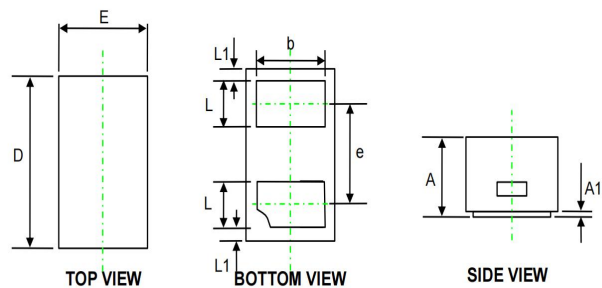
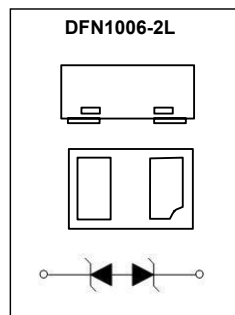


## Features

- Bi-directional ESD protection of one line
- Reverse stand-off voltage: 5V
- Low reverse clamping voltage
- Low leakage current
- Fast response time
- IEC 61000-4-2 (ESD) immunity test :
- Air discharge: ±30kV
- Contact discharge: ±30kV

## Marking Diagram



Symbol	Dimensions In Millimeters (mm)		
	Min.	Typ.	Max.
A	0.44	0.47	0.50
A1	0.00	0.03	0.05
D	0.95	1.00	1.08
E	0.55	0.60	0.68
b	0.40	0.50	0.60
e	-	0.65	-
L	0.20	0.25	0.30
L1	0.05 REF.		

## Description

Designed to protect voltage sensitive electronic components from ESD and other transients. Excellent clamping capability, low leakage, low capacitance, and fast response time provide best in class protection on designs that are exposed to ESD.

The combination of small size, low capacitance, and high level of ESD protection makes them a flexible solution for applications such as HDMI, Display Port TM, and MDDI interfaces. It is designed to replace multiplayer varistors (MLV) in consumer equipments applications such as mobile phone, notebook, PAD, STB, LCD TV etc.

## Applications

- Computers and peripherals
- High speed data lines
- Audio and video equipment
- Cellular handsets and accessories
- Subscriber identity module(SIM) card protection
- Portable electronics
- FireWire
- Other electronics equipments communi- cation systems

## ES05D1MC10

### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)

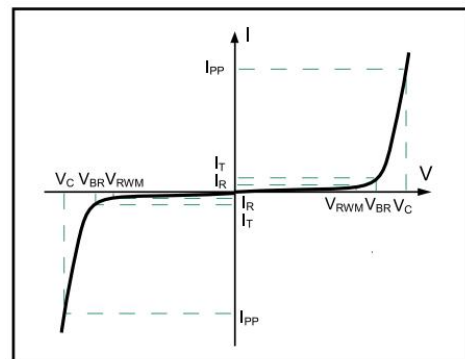
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 $\mu\text{s}$ )	Ppk	80	W
Peak Pulse Current (8/20 $\mu\text{s}$ )	IPP	8	A
ESD per IEC 61000-4-2 (Air)	VESD	$\pm 30$	kV
ESD per IEC 61000-4-2 (Contact)		$\pm 30$	
Operating Temperature Range	TJ	-55to +125	$^\circ\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^\circ\text{C}$

### Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise specified)

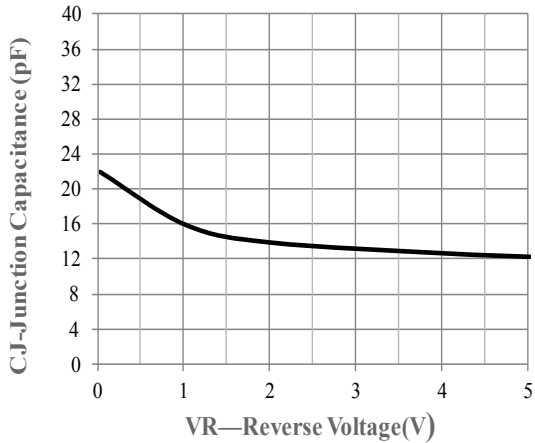
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	$V_{RWM}$				5	V
Breakdown Voltage	VBR	$I_T = 1\text{mA}$	5.6			V
Reverse Leakage Current	$I_R$	$V_{RWM} = \pm 5\text{V}$			0.2	$\mu\text{A}$
Clamping Voltage	$V_C$	$I_{PP} = 8\text{A}$ (8 x 20 $\mu\text{s}$ pulse)			11	V
Junction Capacitance	$C_j$	$V_R = 0\text{V}$ , $f = 1\text{MHz}$			22	pF

### Electronics Parameter

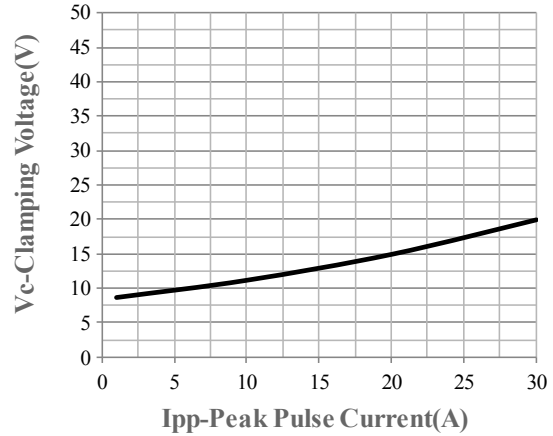
Symbol	Parameter
$I_T$	Test Current
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_C$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$V_{RWM}$	Reverse Standoff Voltage



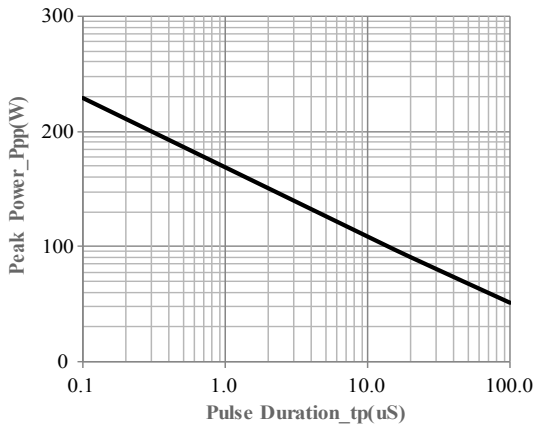
## Typical Performance Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise Specified)



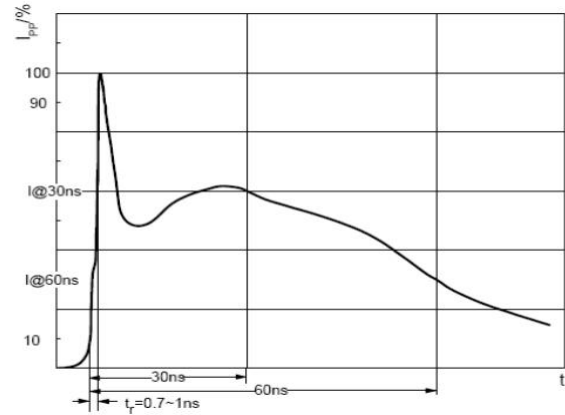
Junction Capacitance vs. Reverse Voltage



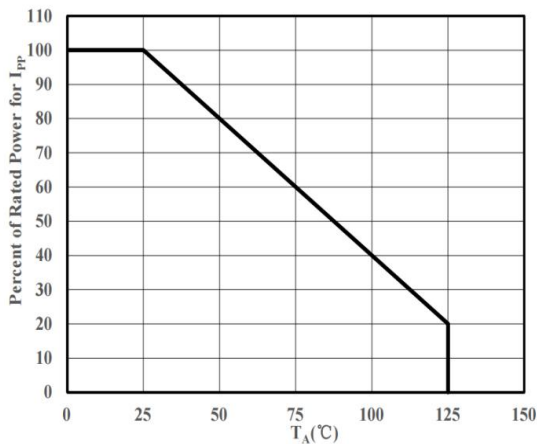
Clamping Voltage vs. Peak Pulse Current



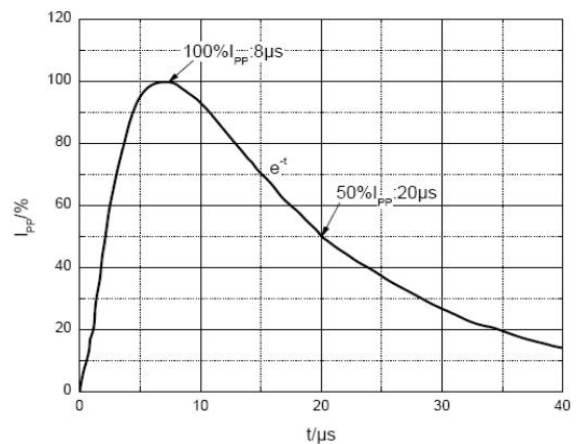
Peak Pulse Power vs. Pulse Time



ESD pulse waveform according to IEC61000-4-2



Power Derating Curve



8/20µs pulse waveform according to IEC 61000-4-5